AMENDMENTS TO THE CLAIMS

1. (Previously Amended) A liquid crystal display comprising:

a plurality of gate lines including first to n^{th} gate lines formed along a first direction;

a plurality of data lines formed along a second direction substantially perpendicular to the first direction and crossing the gate lines;

a plurality of pixel electrodes each formed in a pixel area defined by the gate lines and the data lines, the pixel electrodes indicating pictures under control of the corresponding gate lines; and

a light transmission restricting layer formed beneath at least one of the pixel electrodes positioned between the first and second gate lines and not formed beneath the pixel electrodes positioned between any other gate lines.

Claim 2 (Canceled).

3. (Previously Amended) The liquid crystal display as claimed in claim 1, wherein the light transmission restricting layer is an amorphous silicon layer.

4. (Withdrawn) A method for manufacturing a liquid crystal display, the method comprising:

forming gate lines and a gate electrode on a substrate;

forming a gate insulating film on the substrate, including the gate electrode;

forming a first active layer on the gate insulating film corresponding to an upper portion of the gate electrode and forming a second active layer on the gate insulating film corresponding to a portion where pixel electrodes are to be formed;

forming source/drain electrodes on an upper portion of the first active layer; and

forming a passivation film on the whole surface of the active layer including the source/drain electrodes.

5. (Withdrawn) The method as claimed in claim 4, wherein the first and second active layers are amorphous silicon layers.

6. (Withdrawn) The method as claimed in claim 4, wherein a thickness of the second active layer is changed according to the transmission of light.

7. (Withdrawn) The method as claimed in claim 6, wherein the second active layer is adjusted in area according to an etching speed.

8. (Previously Amended) A liquid crystal display (LCD) device, comprising:

a substrate;

an insulating layer on the substrate;

a plurality of scanning lines (GØ - Gn) extending along a first direction over the substrate;

a plurality of data lines (D1 - Dn) extending along a second direction substantially perpendicular to the first direction over the substrate and crossing the scanning lines (GØ - Gn);

a plurality of switching devices over the substrate arranged in a plurality of rows, each switching device including an active layer formed on the insulating layer, wherein each switching device is connected to one of the scanning lines (GØ - Gn) for controlling a switching of the switching device and one of the data lines (D1 - Dn) for applying data to the switching device, wherein switching devices in each row are connected to a same scanning line, and wherein the rows of switching devices are sequentially scanned by the scanning lines (GØ - Gn);

a plurality of pixel electrodes over the substrate in a plurality of pixel areas defined by the scanning lines (GØ - Gn) and the data lines (D1 - Dn), the pixel electrodes each being connected to a corresponding one of the switching devices; and

a light transmission restricting layer formed directly on the insulating layer and beneath at least one of the plurality of pixel electrodes positioned between the GØ and G1 scanning lines and not formed beneath the plurality of pixel electrodes positioned between any other scanning lines.

9. (Previously Presented) The LCD device of claim 8, wherein the light transmission restricting layer is a semiconductive layer.

10. (Previously Presented) The LCD device of claim 9, wherein the switching devices include an active layer.

11. (Previously Presented) The LCD device of claim 9, wherein the semiconductive layer is an amorphous silicon layer.

Claim 12 (Canceled).

13. (Previously Amended) A method for manufacturing a liquid crystal display, the method comprising:

forming a plurality of scanning lines (GØ - Gn) along a first direction on a substrate;

forming an insulating layer on the substrate on which the scanning lines (GØ - Gn) are formed;

forming a plurality of switching devices on the insulating layer, the forming the plurality of switching devices including forming an active layer for each of the switching devices;

forming a light transmission restricting layer simultaneously with the forming of the active layer;

forming a plurality of data lines (D1 - Dn) along a second direction substantially perpendicular to the first direction on the substrate and crossing the scanning lines (GØ - Gn); and

forming a plurality of pixel electrodes on the substrate in a plurality of pixel areas defined by the scanning lines (GØ - Gn) and the data lines (D1 - Dn), the pixel electrodes each being controlled by one of the scanning lines,

wherein the light transmission restricting layer is formed beneath at least one of the plurality of pixel electrodes positioned between the GØ and G1 scanning lines and is not formed beneath the plurality of pixel electrodes positioned any other scanning lines.

14. (Original) The method of claim 13, further comprising forming a second insulating layer on the light transmission restricting layer before forming the pixel electrodes.

15. (Original) The method of claim 13, further comprising forming a plurality of switching devices on the substrate arranged in a plurality of rows, each switching device connected to one of the scanning lines (GØ - Gn) and one of the data lines (D1 - Dn).

Claim 16 (Canceled).

17. (Previously Presented) The liquid crystal display as claimed in claim 1, wherein the light transmission restricting layer is formed beneath a plurality of pixel electrodes that are controlled by a second gate line among the gate lines.

18. (Previously Presented) The method of claim 13, wherein the light transmission restricting layer is formed beneath the plurality of pixel electrodes that are controlled by a second scanning line (G1) among the scanning lines (GØ - Gn).

19. (Previously Presented) A display device, comprising:

a plurality of pixel regions defined by a plurality of gate lines (first to Nth gate lines) and a plurality of data lines;

first and second sets of pixel electrodes in the pixel regions, each of the first set of the pixel electrodes connected to the first gate line through a thin film transistor and each of the second set of the pixel electrodes connected to one of the second to Nth gate lines through a thin film transistor;

a light transmission restricting layer formed beneath each of the first set of the pixel electrodes and not formed beneath the second set of the pixel electrodes.

20. (Previously Presented) The display device as claimed in claim 19, wherein the light transmission restricting layer is a semiconductor layer of the thin film transistor.

21. (Previously Presented) The display device as claimed in claim 20, wherein the active layer includes silicon.

22. (New) The display device as claimed in claim 1, further comprising:

a plurality of switching devices adjacent to crossing portions of the gate and data lines, each switching device including an active layer, wherein each switching device is connected to one of the gate lines for controlling a switching of the switching device and one of the data lines for applying data to the switching device, wherein switching devices in each row are connected to a same gate line, and wherein the rows of switching devices are sequentially scanned by the gate lines.

23. (New) The display device as claimed in claim 22, wherein the light transmission restricting layer is a semiconductor layer.

24. (New) The display device as claimed in claim 22, wherein the semiconductor layer is same as the active layer of the switching device.